

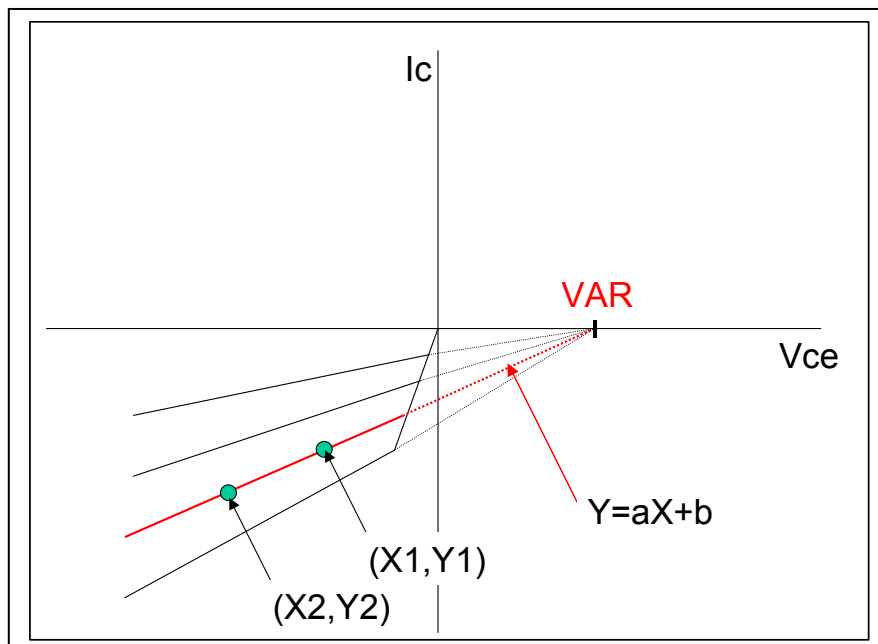
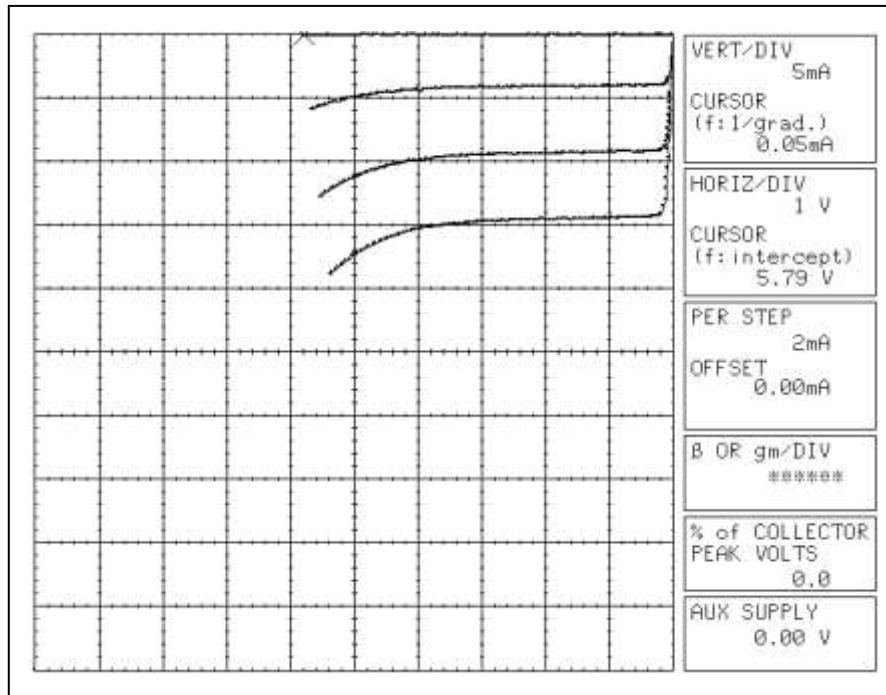
# Device Modeling Report

COMPONENTS: BIPOLAR JUNCTION TRANSISTOR  
PART NUMBER: 2SC945  
MANUFACTURER: NEC

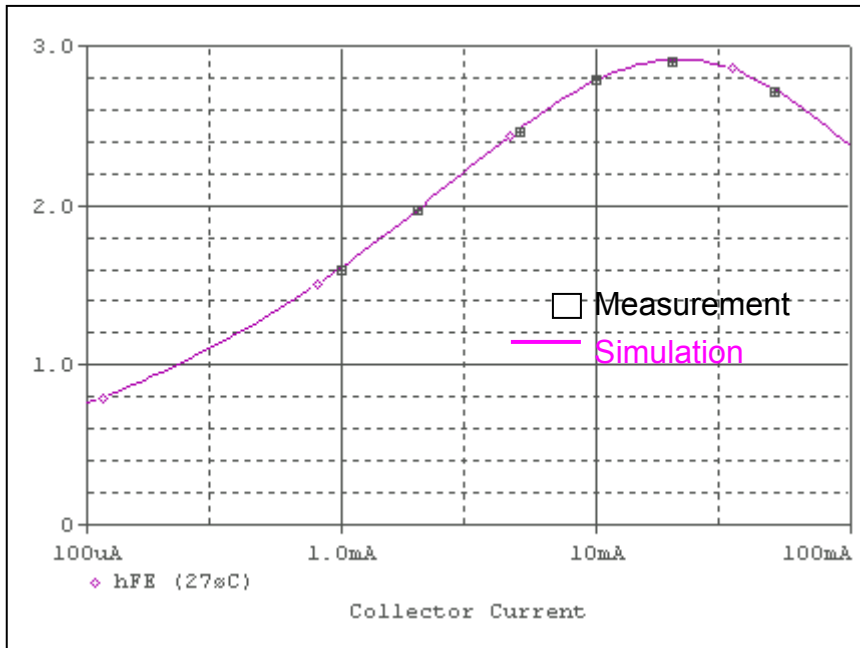


**Bee Technologies Inc.**

# Characteristic

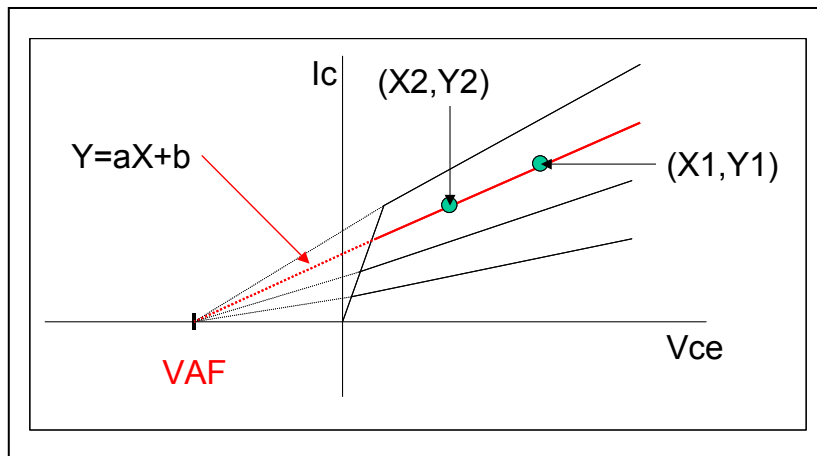
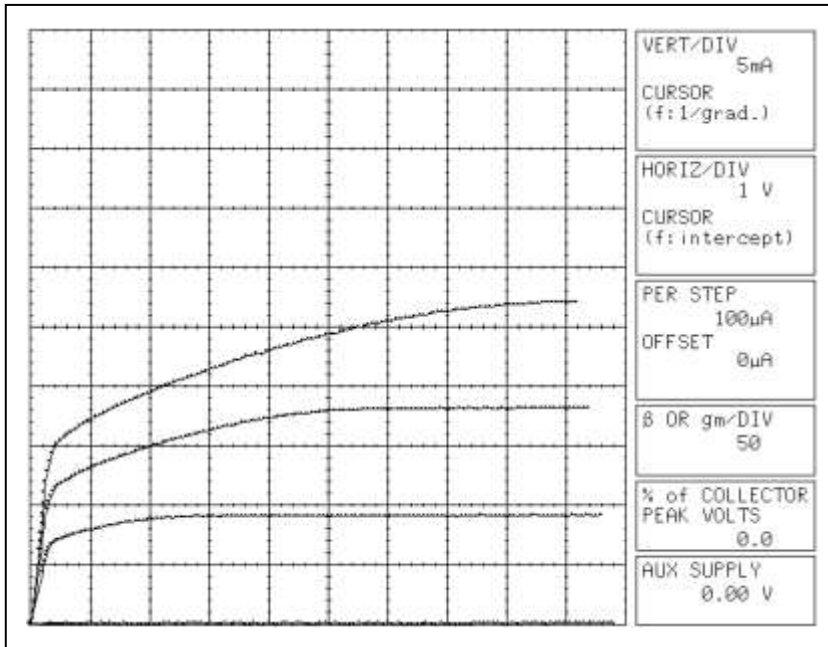


## Reverse DC Beta Characteristic (Ie vs. hFE)

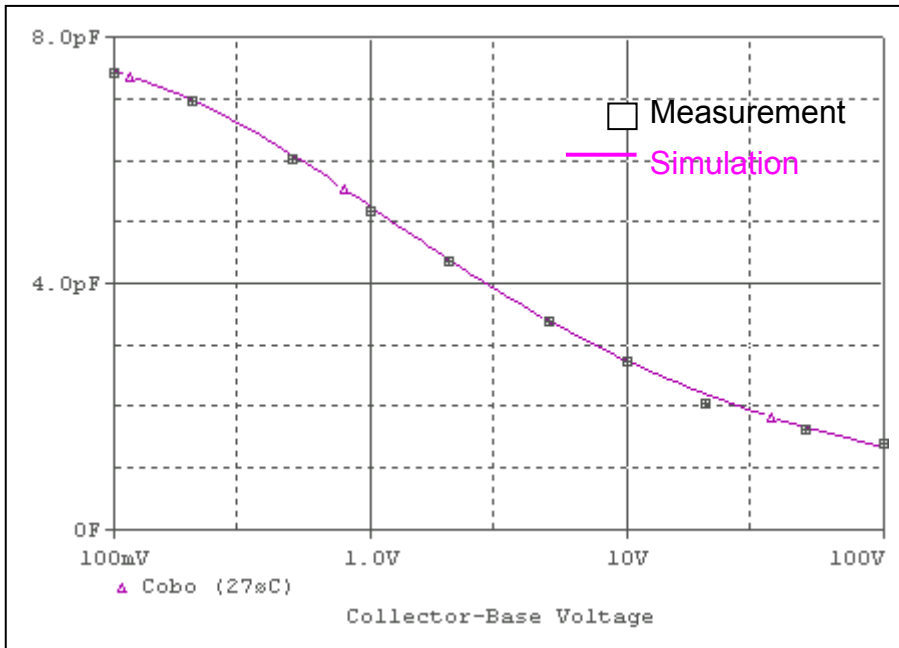


# Forward

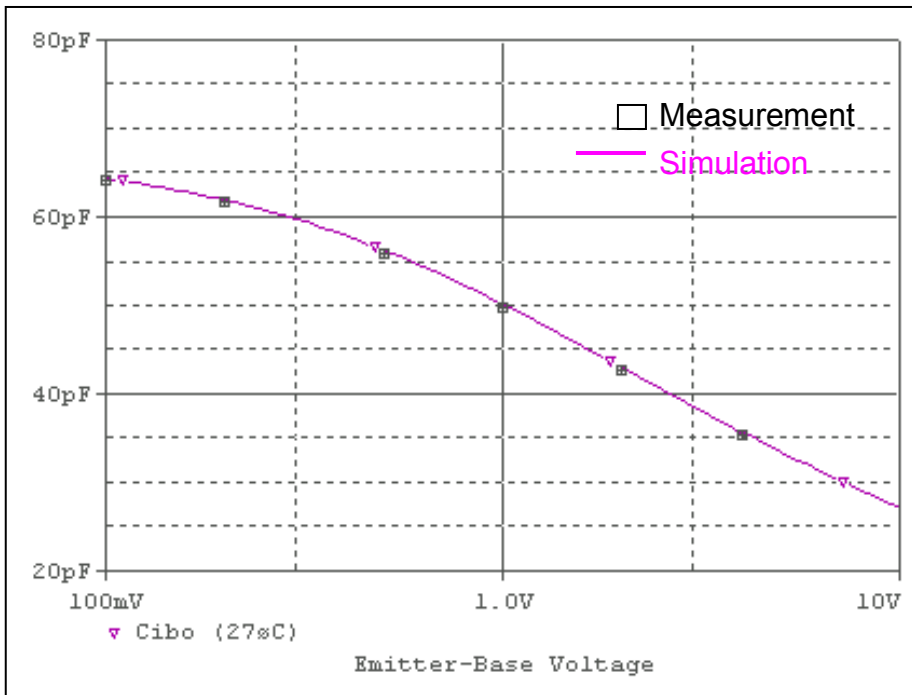
## Forward Early Voltage Characteristic



## C-B Capacitance Characteristic

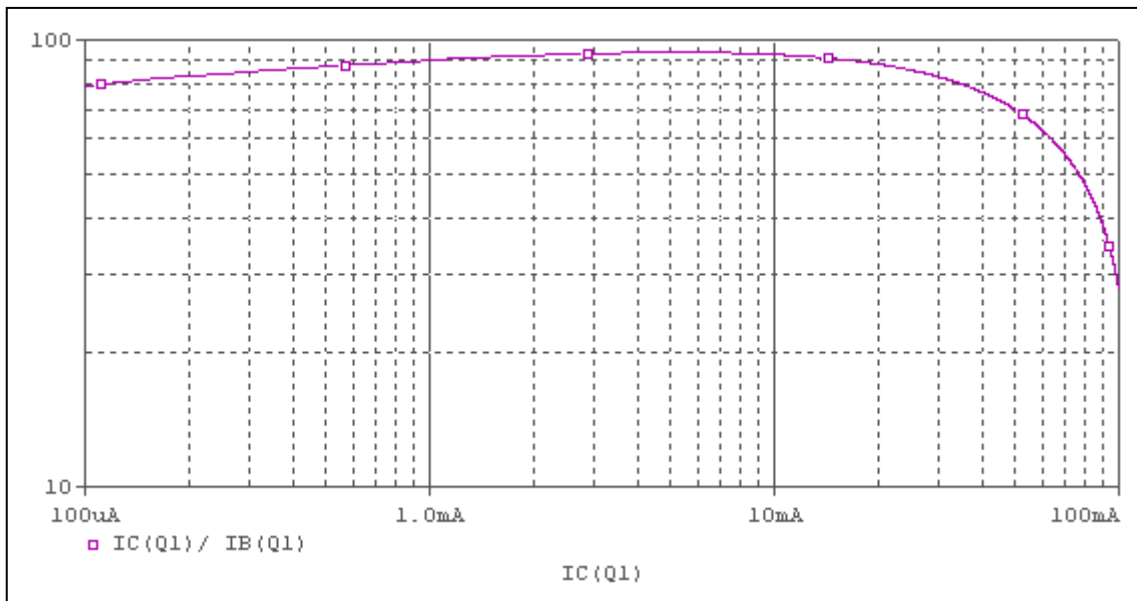


## E-B Capacitance Characteristic

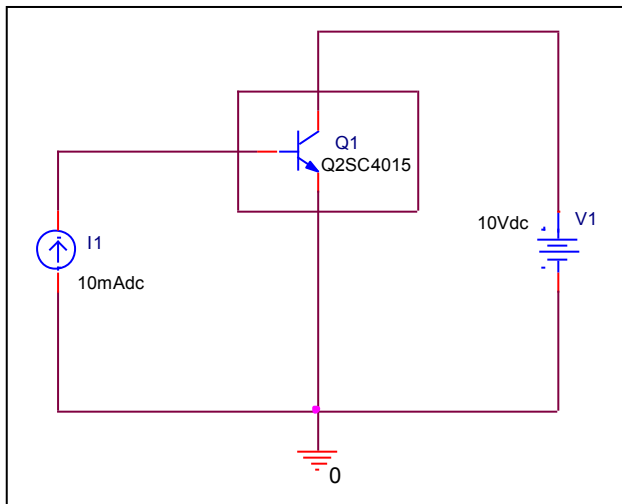


## BJT Ic-hFE characteristics

### Circuit simulation result

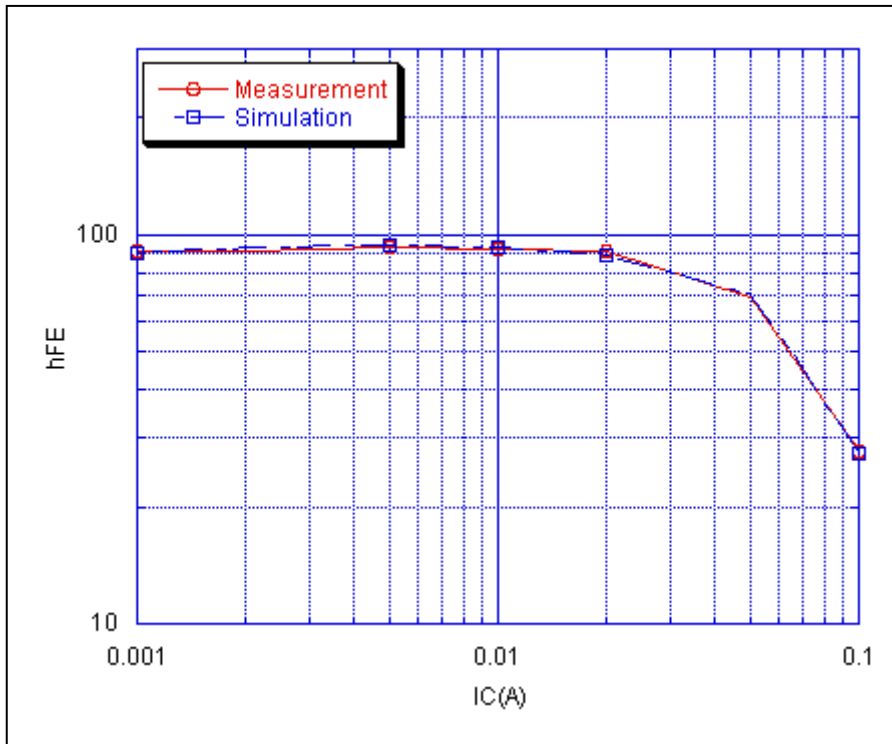


### Evaluation circuit



## Comparison Graph

Circuit simulation result

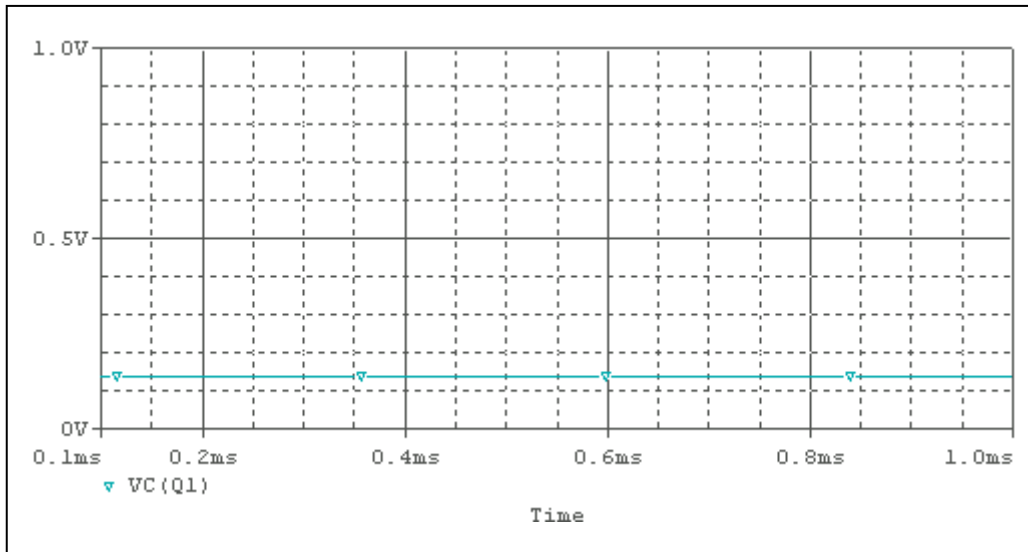


Simulation result

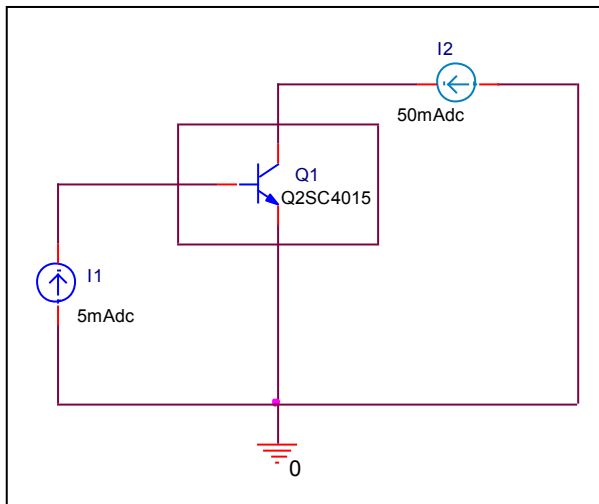
Ic(A)	hFE		%Error
	Measurement	Simulation	
0.001	90.909	90.103	0.886600887
0.002	90.909	92.317	1.548801549
0.005	92.592	93.76	1.261448073
0.01	91.743	92.807	1.159761508
0.02	90.324	88.291	2.250786059
0.05	69.252	69.61	0.516952579
0.1	27.855	27.481	1.342667385

## BJT Vce(sat) voltage Characteristics

### Circuit simulation result



### Evaluation circuit



### Simulation result

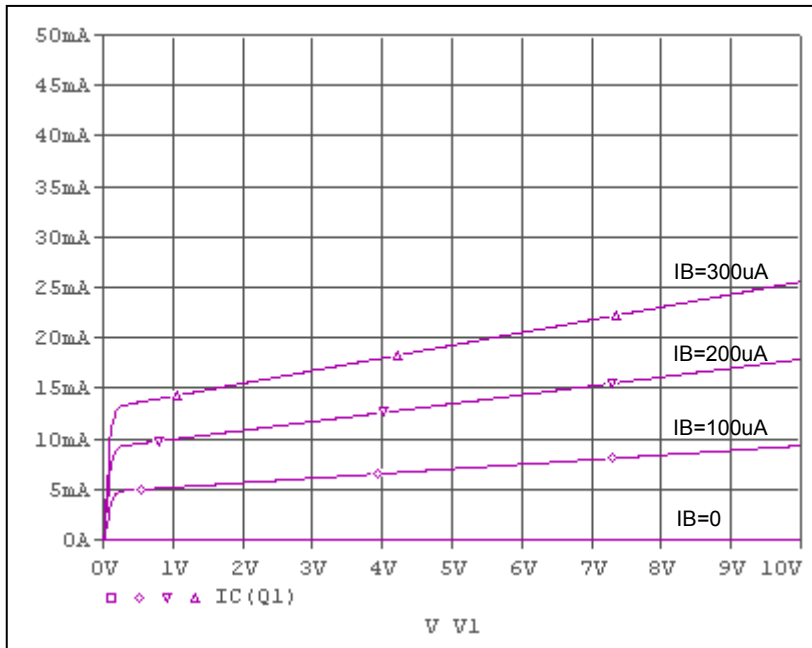
Test condition:  $I_C/I_B = 10$ ,  $I_C=100\text{mA}$

Vce(sat)(V)			Vbe(sat)(V)		
Measurement	Simulation	Error(%)	Measurement	Simulation	Error(%)
1[max]	107.051m	-	1[max]	719.436m	-



## Output Characteristics

### Circuit simulation result



### Evaluation circuit

